



ISO721, ISO721M

SLLS629A-JANUARY 2006-REVISED JANUARY 2006

3.3-V / 5-V HIGH-SPEED DIGITAL ISOLATORS

FEATURES

- 4000-V_(peak) Isolation
 - UL 1577, IEC 60747-5-2 (VDE 0884, Rev. 2)
 - IEC 61010-1 and CSA Approved
 - 50 kV/µs Transient Immunity Typical
- Signaling Rate 0 Mbps to 150 Mbps
 - Low-Propagation Delay
 - Low Pulse-Width Distortion
- **High-Electromagnetic Immunity**
- **Low-Input Current Requirement**
- **Failsafe Output**

Drop-In Replacement for Most Opto and Magnetic Isolators

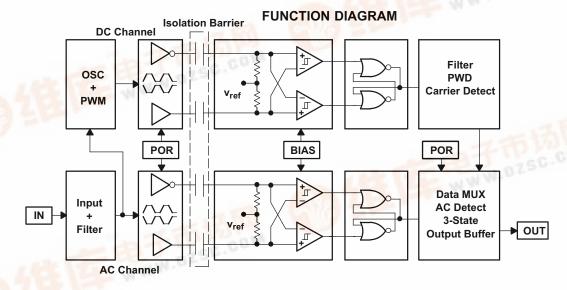
APPLICATIONS

- Industrial Fieldbus
 - Modbus
 - Profibus
 - DeviceNet™ Data Buses
 - Smart Distributed Systems (SDS™)
- **Computer Peripheral Interface** WWW.DZSC.COM
- Servo Control Interface
- **Data Acquisition**

DESCRIPTION

The ISO721 and ISO721M digital isolators have a logic input and output buffer separated by a silicon oxide (SiO₂) insulation barrier. This barrier provides galvanic isolation of up to 4000 V. Used in conjunction with isolated power supplies, these devices prevent noise currents on a data bus or other circuits from entering the local ground, and interfering with or damaging sensitive circuitry.

A binary input signal is conditioned, translated to a balanced signal, then differentiated by the capacitive isolation barrier. Across the isolation barrier, a differential comparator receives the logic transition information, then sets or resets a flip-flop and the output circuit accordingly. A periodic update pulse is sent across the barrier to ensure the proper dc level of the output. If this dc-refresh pulse is not received for more than 4 µs, the input is assumed to be unpowered or not functional, and the failsafe circuit drives the output to a logic high state.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas This truments semiconductor products and disclaimers thereto appears at the end of this data sheet.

DeviceNet is a trademark of Open Devicenet Vendors Association, Inc.

SDS is a trademark of Honeywell.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

DESCRIPTION (CONTINUED)

The symmetry of the dielectric and capacitor within the integrated circuitry provides for close capacitive matching, and allows fast transient voltage changes between the input and output grounds without corrupting the output. The small capacitance and resulting time constant provide for fast operation with signaling rates⁽¹⁾ from 0 Mbps (dc) to 100 Mbps for the ISO721, and 0 Mbps to 150 Mbps with the ISO721M.

These devices require two supply voltages of 3.3-V, 5-V, or any combination. All inputs are 5-V tolerant when supplied from a 3.3-V supply and all outputs are 4-mA CMOS.

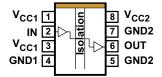
The ISO721 has TTL input thresholds and a noise-filter at the input that prevents transient pulses of up to 2 ns in duration from being passed to the output of the device.

The ISO721M has CMOS V_{CC}/2 input thresholds, but does not have the noise-filter and the additional propagation delay. These features of the ISO721M also provide for reduced jitter operation.

The ISO721 and ISO721M are characterized for operation over the ambient temperature range of -40°C to 125°C.

(1) The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

PACKAGE PIN ASSIGMENTS ISO721D, ISO721MD (TOP VIEW)



ORDERING INFORMATION

PRODUCT	INPUT THRESHOLDS	NOISE FILTER	PACKAGE ⁽¹⁾	PACKAGE DESIGNATOR	MARKED AS	ORDERING NUMBER	GREEN	
ISO721	TTL	YES	SOIC-8	D	D	ISO721	ISO721D (rail)	
130721	IIL	163	3010-6	Ь	130721	ISO721DR (reel)	Pb Free	
100704M	CMOS	NO	0010	6	ICZOAM	ISO721MD (rail)	Sb/Br Free	
ISO721M	CMOS	NO	SOIC-8	U	IS721M	ISO721MDR (reel)		

For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

REGULATORY INFORMATION

VDE	CSA	UL
Certified according to IEC 60747-5-2		Recognized under 1577 Component Recognition Program ⁽¹⁾
File Number: 40014131	File Number: 1698195	File Number: 181974

(1) Production tested \geq 3000 V_{RMS} for 1 second in accordance with UL 1577.



ABSOLUTE MAXIMUM RATINGS(1)(2)

					UNIT	
V_{CC}	Supply voltage, V _C	_{C1} , V _{CC2}			–0.5 V to 6 V	
VI	Voltage at IN or Ol	Voltage at IN or OUT terminal				
Io	Output Current	±15 mA				
ESD	Electrostatic	Human Body Model	JEDEC Standard 22, Test Method A114-C.01	All ning	±2 kV	
ESD	discharge	Charged Device Model	JEDEC Standard 22, Test Method C101	All pins	±1 kV	
TJ	Maximum junction temperature				170°C	

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

			MIN	TYP MAX	UNIT	
V	Cumply valtage V V		4.5	5.5	V	
V _{CC}	Supply voltage, V _{CC1} , V _{CC2}		3	3.6	V	
I _{OH}	Output ourrent			4	A	
I _{OL}	Output current		-4		mA	
	Input pulse width	ISO721	10			
t _{ui}	input puise wiath	ISO721M	6.67		ns	
V _{IH}	High-level input voltage (IN)	ISO721	2	V _{CC}	V	
V _{IL}	Low-level input voltage (IN)	150721	0	0.8	V	
V_{IH}	High-level input voltage (IN)	IOS721M	0.7 V _{CC}	V_{CC}	V	
V _{IL}	Low-level input voltage (IN)	105721101	0	0.3 V _{CC}	V	
T_{J}	Junction temperature	See the Thermal Characteristics table		150	°C	
Н	External magnetic field intensity pe certification		1000	A/m		

IEC 60747-5-2 INSULATION CHARACTERISTICS(1)

	PARAMETER	TEST CONDITIONS	SPECIFICATIONS	UNIT
V _{IORM}	Maximum working insulation voltage		560	V
V_{PR}		After Input/Output Safety Test Subgroup 2/3 $V_{PR} = V_{IORM} \times 1.2$, t = 10 s, Partial discharge < 5 pC	672	V
	Input to output test voltage	Method a, $V_{PR} = V_{IORM} \times 1.6$, Type and sample test with t = 10 s, Partial discharge < 5 pC	896	V
		Method b1, $V_{PR} = V_{IORM} \times 1.875$, 100 % Production test with t = 1 s, Partial discharge < 5 pC	1050	V
V _{IOTM}	Transient overvoltage	t = 60 s	4000	V
R _S	Insulation resistance	$V_{IO} = 500 \text{ V at T}_{S}$	>10 ⁹	Ω
	Pollution degree		2	

⁽¹⁾ Climatic Classification 40/125/21

⁽²⁾ This isolator is suitable for basic insulation applications within the safety limiting data. Maintenance of the safety data must be ensured by means of protective circuitry.



ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} 5-V OPERATION

over recommended operating conditions (unless otherwise noted)

	PARAMET	ΓER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	\/ aunnhy aurrant	Quiescent	V – V or 0 V No load		0.5	1	mA
I _{CC1}	V _{CC1} supply current	25 Mbps	$V_I = V_{CC}$ or 0 V, No load		2	3.5	ША
	\/ aumply augrent	Quiescent	V V or 0 V No load		8	12	mΑ
I _{CC2} V _{CC2} supply current	25 Mbps	$V_I = V_{CC}$ or 0 V, No load		10	14	mA	
\/	V _{OH} High-level output voltage		I _{OH} = -4 mA, See Figure 1	$V_{CC} - 0.8$	4.6		٧
V _{OH}	nigh-level output voltage		$I_{OH} = -20 \mu A$, See Figure 1	V _{CC} - 0.1	5		V
\/	Low lovel output voltage		I _{OL} = 4 mA, See Figure 1		0.2	0.4	V
V _{OL}	Low-level output voltage		I_{OL} = 20 μ A, See Figure 1		0	0.1	V
$V_{I(HYS)}$	Input voltage hysteresis				150		mV
I _{IH}	High-level input current		IN at 2 V			10	
I_{IL}	L Low-level input current		IN at 0.8 V	-10	-10 μ		μA
CI	C _I Input capacitance to ground		$V_I = 0.4 \sin (4E6\pi t) + 0.5 V$		1		pF
CMTI	Common-mode transient	immunity	V _I = V _{CC} or 0 V, See Figure 3	25	50		kV/µs

SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} 5-V OPERATION

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
t _{PLH}	Propagation delay, low-to-high-level output			13	17	24		
t _{PHL}	Propagation delay, high-to-low-level output	ISO721		13	17	24	ns	
t _{sk(p)}	Pulse skew t _{PHL} - t _{PLH}		Coo Figure 4		0.5	2		
t _{PLH}	Propagation delay, low-to-high-level output		See Figure 1	8	10	16		
t _{PHL}	Propagation delay, high-to-low-level output	ISO721M		8	10	16	ns	
t _{sk(p)}	Pulse skew t _{PHL} - t _{PLH}				0.5	1		
t _{sk(pp)} ⁽¹⁾	Part-to-part skew				0	3	ns	
t _r	Output signal rise time		Soo Figure 1		1		ns	
t _f	Output signal fall time		See Figure 1		1			
t _{fs}	Failsafe output delay time from input power loss		See Figure 2		3		μs	
			100 Mbps NRZ data input See Figure 4	2				
		ISO721	100 Mbps unrestricted bit run length data input See Figure 4		3			
t _{jit(PP)}	Peak-to-peak eye-pattern jitter		150 Mbps NRZ data input See Figure 4		1	ns		
		ISO721M	150 Mbps unrestricted bit run length data input See Figure 4		2			

⁽¹⁾ $t_{sk(PP)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.



ELECTRICAL CHARACTERISTICS: V_{CC1} at 5-V, V_{CC2} at 3.3-V OPERATION

over recommended operating conditions (unless otherwise noted)

	PARAME	ΓER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	V aupply aurrent	Quiescent	V - V or 0 V No load		0.5	1	mA
I _{CC1}	V _{CC1} supply current	25 Mbps	$V_I = V_{CC}$ or 0 V, No load		2	3.5	ША
	\/ august august	Quiescent	V V or O.V. No load		4	6.5	mA
I _{CC2} V _{CC2} supply current	25 Mbps	$V_I = V_{CC}$ or 0 V, No load		5	7.5	mA	
V	V _{OH} High-level output voltage		I _{OH} = -4 mA, See Figure 1	V _{CC} - 0.4	3		V
V _{OH}	nigh-level output voltage		$I_{OH} = -20 \mu A$, See Figure 1	V _{CC} - 0.1	3.3		V
V	I am laval autout valtage		I _{OL} = 4 mA, See Figure 1		0.2	0.4	V
V _{OL}	Low-level output voltage		I_{OL} = 20 μ A, See Figure 1		0	0.1	V
$V_{I(HYS)}$	Input voltage hysteresis				150		mV
I _{IH}	High-level input current		IN at 2 V			10	
$I_{\rm IL}$	IL Low-level input current		IN at 0.8 V	-10			μΑ
CI	Input capacitance to grou	nd	$V_I = 0.4 \sin (4E6\pi t) + 0.5 V$		1		pF
CMTI	Common-mode transient	immunity	V _I = V _{CC} or 0 V, See Figure 3	25	40		kV/μs

SWITCHING CHARACTERISTICS: V_{CC1} at 5-V, V_{CC2} at 3.3-V OPERATION

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
t _{PLH}	Propagation delay, low-to-high-level output			15	19	30		
t _{PHL}	Propagation delay, high-to-low-level output	ISO721		15	19	30	ns	
t _{sk(p)}	Pulse skew t _{PHL} - t _{PLH}		Con Figure 4		0.5	3		
t _{PLH}	Propagation delay, low-to-high-level output		See Figure 1	10	12	20		
t _{PHL}	Propagation delay, high-to-low-level output	ISO721M		10	12	20	ns	
t _{sk(p)}	Pulse skew t _{PHL} - t _{PLH}				0.5	1		
t _{sk(pp)} (1)					0	5	ns	
t _r	Output signal rise time	Coo Figure 4		2		20		
t _f	Output signal fall time		See Figure 1		2		ns	
t _{fs}	Failsafe output delay time from input power loss		See Figure 2		3		μs	
			100 Mbps NRZ data input See Figure 4		2			
		ISO721	100 Mbps unrestricted bit run length data input See Figure 4		3			
t _{jit(pp)}	Peak-to-peak eye-pattern jitter		150 Mbps NRZ data input See Figure 4		1	ns		
		ISO721M	150 Mbps unrestricted bit run length data input See Figure 4		2		l	

⁽¹⁾ $t_{sk(PP)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.



ELECTRICAL CHARACTERISTICS: V_{CC1} at 3.3-V, V_{CC2} at 5-V OPERATION

over recommended operating conditions (unless otherwise noted)

	PARAME	TER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	\/ aummby augment	Quiescent	V V or 0 V No load		0.3	0.5	mA
I _{CC1}	V _{CC1} supply current	25 Mbps	$V_I = V_{CC}$ or 0 V, No load		1	1.5	IIIA
	\/ augustu august	Quiescent	V V or 0 V No lood		8	12	A
I _{CC2}	I _{CC2} V _{CC2} supply current	25 Mbps	$V_I = V_{CC}$ or 0 V, No load		10	14	mA
.,	Lligh level output voltage	h-level output voltage		$V_{CC} - 0.8$	4.6		V
V _{OH}	V _{OH} — nigri-level output voltage	;	I _{OH} = -20 μA, See Figure 1	V _{CC} - 0.1	5		V
\/	Low lovel output voltogo		I _{OL} = 4 mA, See Figure 1		0.2	0.4	V
V _{OL}	Low-level output voltage		I_{OL} = 20 μ A, See Figure 1		0	0.1	V
V _{I(HYS)}	Input voltage hysteresis				150		mV
I _{IH}	High-level input current		IN at 2 V			10	
I _{IL}	Low-level input current		IN at 0.8 V	-10			μA
C _I	Input capacitance to gro	und	V _I = 0.4 sin (4E6πt) + 0.5 V		1		pF
CMTI	Common-mode transien	t immunity	V _I = V _{CC} or 0 V, See Figure 3	25	40		kV/μs

SWITCHING CHARACTERISTICS: V_{CC1} at 3.3-V, V_{CC2} at 5-V OPERATION

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
t _{PLH}	Propagation delay, low-to-high-level output			15	17	30		
t _{PHL}	Propagation delay, high-to-low-level output	ISO721		15	17	30	ns	
t _{sk(p)}	Pulse skew t _{PHL} - t _{PLH}		Coo Figure 4		0.5	2		
t _{PLH}	Propagation delay, low-to-high-level output		See Figure 1	10	12	21		
t _{PHL}	Propagation delay, high-to-low-level output	ISO721M		10	12	21	ns	
t _{sk(p)}	Pulse skew t _{PHL} - t _{PLH}				0.5	1		
t _{sk(pp)} (1)					0	5	ns	
t _r	Output signal rise time Output signal fall time		Coo Figure 4		1		ns	
t _f			See Figure 1		1			
t _{fs}	Failsafe output delay time from input power loss		See Figure 2		3		μs	
			100 Mbps NRZ data input See Figure 4		2			
		ISO721	100 Mbps unrestricted bit run length data input See Figure 4		3			
t _{jit(pp)}	Peak-to-peak eye-pattern jitter		150 Mbps NRZ data input See Figure 4		1	ns		
		ISO721M	150 Mbps unrestricted bit run length data input See Figure 4		2			

⁽¹⁾ $t_{sk(PP)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.



ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3-V OPERATION

over recommended operating conditions (unless otherwise noted)

	PARAME	TER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
	V supply surrent	Quiescent	V – V or 0 V No load		0.3	0.5	mA	
I _{CC1}	V _{CC1} supply current	25 Mbps	$V_I = V_{CC}$ or 0 V, No load		1	1.5	ША	
	\/ aumphy aumment	Quiescent	V V or O.V. No lood		4	6.5	A	
I _{CC2} V _{CC2} supply current	25 Mbps	$V_I = V_{CC}$ or 0 V, No load		5	7.5	mA		
V Ligh lovel output voltage		~~	I _{OH} = -4 mA, See Figure 1	V _{CC} - 0.4	3		V	
V _{OH}	High-level output voltage	ge	I _{OH} = -20 μA, See Figure 1	V _{CC} - 0.1	3.3		V	
V	Laurianal antonit nalta		I _{OL} = 4 mA, See Figure 1		0.2	0.4	V	
V _{OL}	Low-level output voltag	je	I _{OL} = 20 μA, See Figure 1		0	0.1	V	
V _{I(HYS)}	Input voltage hysteresi	S			150		mV	
I _{IH}	High-level input curren	t	IN at 2 V			10		
I _{IL}	Low-level input current		IN at 0.8 V	-10			μΑ	
C _I	C _I Input capacitance to ground		$V_I = 0.4 \sin (4E6\pi t) + 0.5 V$		1		pF	
CMTI	Common-mode transie	nt immunity	V _I = V _{CC} or 0 V, See Figure 3	25	40		kV/μs	

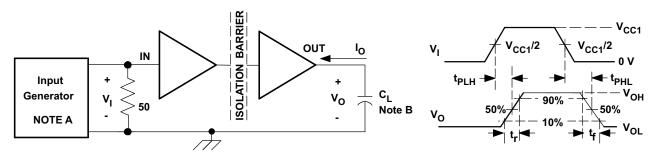
SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3-V OPERATION

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
t _{PLH}	Propagation delay, low-to-high-level output			17	20	34	
t _{PHL}	Propagation delay, high-to-low-level output	ISO721		17	20	34	ns
t _{sk(p)}	Pulse skew t _{PHL} - t _{PLH}		Coo Figure 4		0.5	3	
t _{PLH}	Propagation delay, low-to-high-level output		See Figure 1	10	12	25	
t _{PHL}	Propagation delay, high-to-low-level output	ISO721M		10	12	25	ns
t _{sk(p)}	Pulse skew t _{PHL} - t _{PLH}				0.5	1	
t _{sk(pp)} ⁽¹⁾	Part-to-part skew			0	5.5	ns	
t _r	Output signal rise time	Con Figure 4		2			
t _f	Output signal fall time	See Figure 1		2		ns	
t _{fs}	Failsafe output delay time from input power loss	See Figure 2		3		μs	
			100 Mbps NRZ data input See Figure 4		2		
t _{jit(pp)}	Peak-to-peak eye-pattern jitter	ISO721	100 Mbps unrestricted bit run length data input See Figure 4		3		
		ISO721M	150 Mbps NRZ data input See Figure 4	1			ns
			150 Mbps unrestricted bit run length data input See Figure 4		2		

⁽¹⁾ $t_{sk(PP)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.



PARAMETER MEASUREMENT INFORMATION



- A. The input pulse is supplied by a generator having the following characteristics:
 - PRR ≤ 50 kHz, 50% duty cycle
 - t_r ≤ 3 ns
 - t_f ≤ 3 ns
 - $Z_O = 50 \Omega$.
- B. $C_L = 15 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 1. Switching Characteristic Test Circuit and Voltage Waveforms

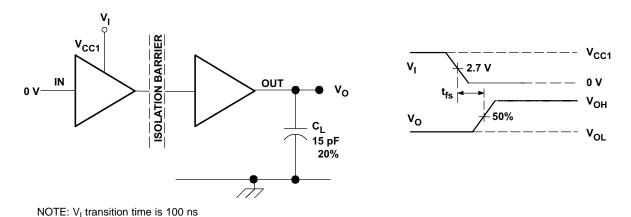
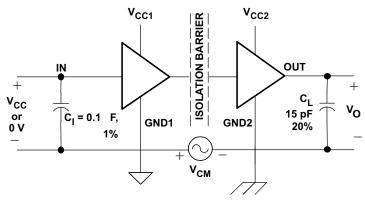


Figure 2. Failsafe Delay Time Test Circuit and Voltage Waveforms

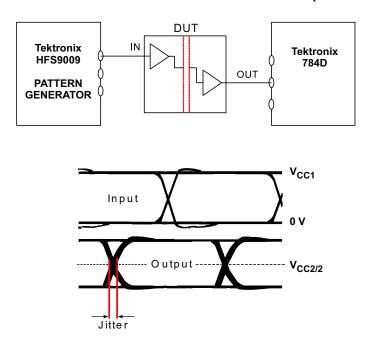


NOTE: Pass/Fail criteria is no change in Vo.

Figure 3. Common-Mode Transient Immunity Test Circuit and Voltage Waveform



PARAMETER MEASUREMENT INFORMATION (continued)



NOTE: Bit pattern run length is 2^{16} - 1. Transition Time is 800 ps. NRZ data input has no more than five consecutive 1s or 0s.

Figure 4. Peak-to-Peak Eye-Pattern Jitter Test Circuit and Voltage Waveform



DEVICE INFORMATION

PACKAGE CHARACTERISTICS

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(101)	Minimum air gap (Clearance) (1)	Shortest terminal to terminal distance through air	4.8			mm
L(102)	Minimum external tracking (Creepage)	Shortest terminal to terminal distance across the package surface	4.3			mm
C _{TI}	Tracking resistance (comparative tracking index)	DIN IEC 60112/VDE 0303 Part 1	≥ 175			V
	Minimum internal gap (internal clearance)	Distance through insulation	0.008			mm
R _{IO}	Isolation resistance	Input to output, $V_{\rm IO}$ = 500 V, all pins on each side of the barrier tied together creating a two-terminal device		>10 ¹²		Ω
C _{IO}	Barrier capacitance Input-to-output	V _I = 0.4 sin (4E6πt)		1		pF
C _I	Input capacitance to ground	V _I = 0.4 sin (4E6πt)		1		pF

⁽¹⁾ Creepage and clearance requirements are applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed circuit board do not reduce this distance.

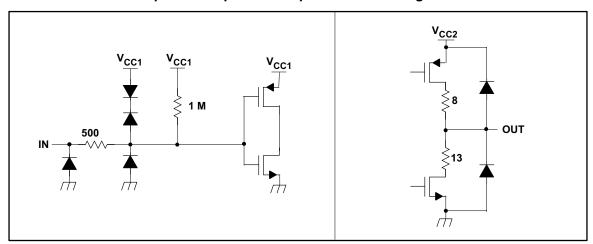
Creepage and clearance on a printed circuit board become equal according to the measurement techniques shown in the Isolation

IEC 60664-1 RATINGS TABLE

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic isolation group	Material group	Illa
Installation classification	Rated mains voltage ≤150 VRMS	I-IV
installation classification	Rated mains voltage ≤300 VRMS	I-III

DEVICE I/O SCHEMATIC

Equivalent Input and Output Schematic Diagrams



Glossary. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.



IEC SAFETY LIMITING VALUES

Safety limiting intends to prevent potential damage to the isolator barrier upon failure of input or output circuitry. A failure of the IO can allow low resistance to ground or the supply, and without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Safaty input, output, or aupply ourrent	$\theta_{JA} = 263^{\circ}\text{C/W}, \ V_{I} = 5.5 \ \text{V}, \ T_{J} = 170^{\circ}\text{C}, \ T_{A} = 25^{\circ}\text{C}$			100	m Λ
IS	Safety input, output, or supply current	$\theta_{JA} = 263^{\circ}\text{C/W}, \ V_{I} = 3.6 \ \text{V}, \ T_{J} = 170^{\circ}\text{C}, \ T_{A} = 25^{\circ}\text{C}$			153	mA
T _S	Maximum case temperature				150	°C

The safety-limiting constraint is the absolute maximum junction temperature specified in the absolute maximum ratings table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The junction-to-air thermal resistance in the Thermal Characteristics table is that of a device installed in the JESD51-3, Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages and is conservative. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

THERMAL CHARACTERISTICS (over recommended operating conditions unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
0			Low-K Thermal Resistance ⁽¹⁾		263		°C/W
θ_{JA}	Junction-to-Air		High-K Thermal Resistance ⁽¹⁾		125		°C/W
θ_{JB}	Junction-to-Board Thermal Resistance				44		°C/W
θ_{JC}	Junction-to-Case Thermal Resistance				75		°C/W
D	Device Power Dissipation	ISO721	$V_{\rm CC1} = V_{\rm CC2} = 5.5$ V, $T_{\rm J} = 150^{\circ}{\rm C}$, $C_{\rm L} = 15$ pF, Input a 100 Mbps 50% duty cycle square wave			159	m1/1/
P _D	FD Device Fower Dissipation	ISO721M	$V_{CC1} = V_{CC2} = 5.5 \text{ V}, T_J = 150^{\circ}\text{C},$ $C_L = 15 \text{ pF}, \text{ Input a 150 Mbps 50\% duty}$ cycle square wave			195	mW

⁽¹⁾ Tested in accordance with the Low-K or High-K thermal metric definition of EIA/JESD51-3 for leaded surface mount packages.

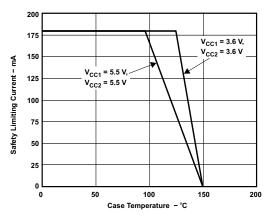


Figure 5. θ_{JC} THERMAL DERATING CURVE per IEC 60747-5-2



FUNCTION TABLE

ISO721 and ISO721M(1)

V _{CC1}	V _{CC2}	INPUT (IN)	OUTPUT (OUT)
		Н	Н
PU	PU	L	L
		Open	Н
PD	PU	X	Н
PU	PD	X	X

(1) PU = Powered Up ($V_{CC} \ge 3$ V); PD = Powered Down ($V_{CC} \le 2.5$ V); X = Irrelevant; H = High Level; L = Low Level

TYPICAL CHARACTERISTICS

RMS SUPPLY CURRENT vs SIGNALING RATE

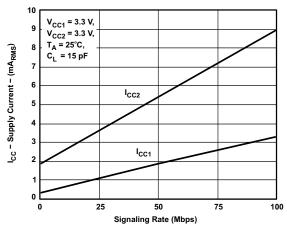


Figure 6.

RMS SUPPLY CURRENT vs SIGNALING RATE

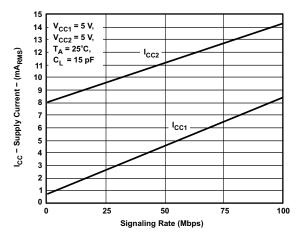


Figure 7.

PROPAGATION DELAY vs FREE-AIR TEMPERATURE

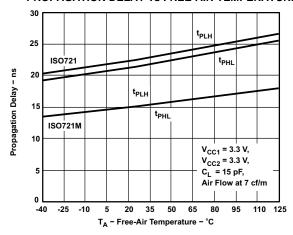


Figure 8.

PROPAGATION DELAY vs FREE-AIR TEMPERATURE

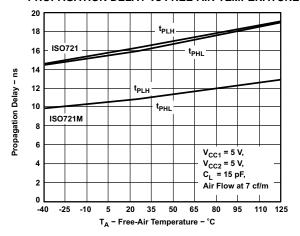


Figure 9.



TYPICAL CHARACTERISTICS (continued)

ISO721 INPUT THRESHOLD VOLTAGE vs FREE-AIR TEMPERATURE

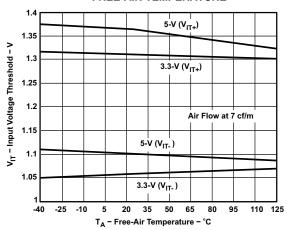


Figure 10.

ISO721M INPUT THRESHOLD VOLTAGE vs FREE-AIR TEMPERATURE

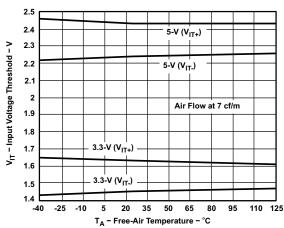


Figure 11.

V_{CC1} FAILSAFE THRESHOLD vs FREE-AIR TEMPERATURE

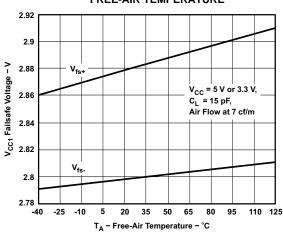


Figure 12.

HIGH-LEVEL OUTPUT CURRENT vs HIGH-LEVEL OUTPUT VOLTAGE

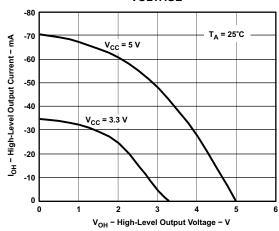


Figure 13.

LOW-LEVEL OUTPUT CURRENT vs LOW-LEVEL OUTPUT VOLTAGE

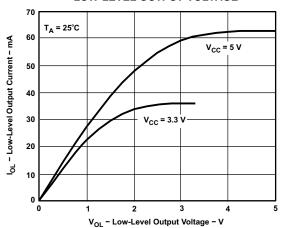


Figure 14.



APPLICATION INFORMATION

MANUFACTURER CROSS-REFERENCE DATA

The ISO721 and ISO721M isolators have the same functional pin-out as most other vendors, and they are often pin-for-pin drop-in replacements. The notable differences in the products are propagation delay, signaling rate, power consumption, and transient protection rating. Table 1 is used as a guide for replacing other isolators with the ISO72xx family of single channel isolators.

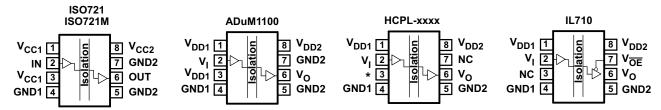


Figure 15. Pin Cross Reference

Table 1. CROSS REFERENCE

ISOLATOR	PIN 1	PIN 2	PIN 3	PIN 4	PIN 5	PIN 6	PIN 7	PIN 8
ISO721 (1)(2)	V _{CC1}	IN	V _{CC1}	GND1	GND2	OUT	GND2	V _{CC2}
ADuM1100 ⁽¹⁾ (2)	V _{DD1}	V _I	V_{DD1}	GND1	GND2	Vo	GND2	V_{DD2}
HCPL-xxxx	V _{DD1}	VI	*Leave Open ⁽³⁾	GND1	GND2	Vo	NC	V_{DD2}
IL710	V _{DD1}	V _I	NC ⁽⁴⁾	GND1	GND2	Vo	V _{OE}	V_{DD2}

- (1) The ISO721 and ISO721M pin 1 and pin 3 are internally connected together. Either or both may be used as V_{CC1} .
- (2) The ISO721 and ISO721M pin 5 and pin 7 are internally connected together. Either or both may be used as GND2.
- (3) Pin 3 of the HCPL devices must be left open. This is not a problem when substituting an ISO721 or ISO721M device since the extra V_{CC1} on pin 3 may be left an open circuit as well.
- (4) Pin 3 of the IL710 must not be tied to ground on the circuit board since this shorts the ISO721 and ISO721M V_{CC1} to ground. The IL710 pin 3 may only be tied to V_{CC} or left open to drop in an ISO721 or ISO721M.

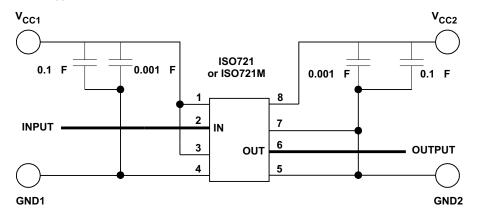
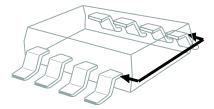


Figure 16. Basic Application Circuit

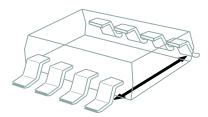


ISOLATION GLOSSARY

Creepage Distance— The shortest path between two conductive input to output leads measured along the surface of the insulation. The shortest distance path is found around the end of the package body.



Clearance— The shortest distance between two conductive input to output leads measured through air (line of sight).



Input-to Output Barrier Capacitance -- The total capacitance between all input terminals connected together, and all output terminals connected together.

Input-to Output Barrier Resistance -- The total resistance between all input terminals connected together, and all output terminals connected together.

Primary Circuit -- An internal circuit directly connected to an external supply mains or other equivalent source which supplies the primary circuit electric power.

Secondary Circuit -- A circuit with no direct connection to primary power, and derives its power from a separate isolated source.

Comparative Tracking Index (CTI) -- CTI is an index used for electrical insulating materials which is defined as the numerical value of the voltage which causes failure by tracking during standard testing. Tracking is the process that produces a partially conducting path of localized deterioration on or through the surface of an insulating material as a result of the action of electric discharges on or close to an insulation surface -- the higher CTI value of the insulating material, the smaller the minimum creepage distance.

Generally, insulation breakdown occurs either through the material, over its surface, or both. Surface failure may arise from flashover or from the progressive degradation of the insulation surface by small localized sparks. Such sparks are the result of the breaking of a surface film of conducting contaminant on the insulation. The resulting break in the leakage current produces an overvoltage at the site of the discontinuity, and an electric spark is generated. These sparks often cause carbonization on insulation material and lead to a carbon track between points of different potential. This process is known as *tracking*.



ISOLATION GLOSSARY (continued)

Insulation:

Operational insulation -- Insulation needed for the correct operation of the equipment.

Basic insulation -- Insulation to provide basic protection against electric shock.

Supplementary insulation -- Independent insulation applied in addition to basic insulation in order to ensure protection against electric shock in the event of a failure of the basic insulation.

Double insulation -- Insulation comprising both basic and supplementary insulation.

Reinforced insulation -- A single insulation system which provides a degree of protection against electric shock equivalent to double insulation.

Pollution Degree:

Pollution Degree 1 -- No pollution, or only dry, nonconductive pollution occurs. The pollution has no influence.

Pollution Degree 2 -- Normally, only nonconductive pollution occurs. However, a temporary conductivity caused by condensation must be expected.

Pollution Degree 3 -- Conductive pollution occurs or dry nonconductive pollution occurs which becomes conductive due to condensation which is to be expected.

Pollution Degree 4- Continuous conductivity occurs due to conductive dust, rain, or other wet conditions.

Installation Category:

Overvoltage Category -- This section is directed at insulation co-ordination by identifying the transient overvoltages which may occur, and by assigning 4 different levels as indicated in IEC 60664.

- I: Signal Level -- Special equipment or parts of equipment.
- II: Local Level -- Portable equipment etc.
- III: Distribution Level -- Fixed installation
- IV: Primary Supply Level -- Overhead lines, cable systems

Each category should be subject to smaller transients than the category above.



PACKAGE OPTION ADDENDUM

10-Feb-2006

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
ISO721D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO721DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO721DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO721DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO721MD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO721MDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO721MDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
ISO721MDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

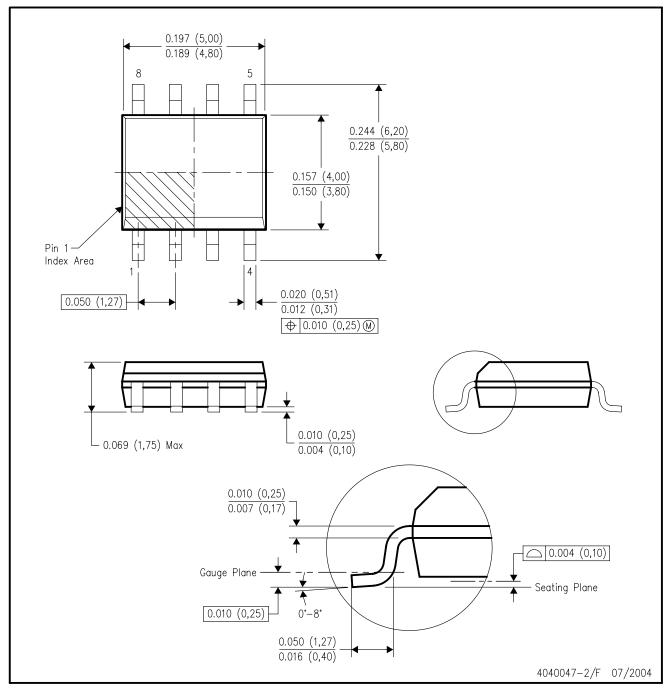
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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D (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-012 variation AA.



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